

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-30. (Canceled)

31. (Currently Amended) A semiconductor device comprising:

a first substrate;

a thin film transistor over said first substrate;

~~a source region, a drain region and a channel formation region in said thin film transistor;~~

~~a source wiring electrically connected with said source region;~~

a second substrate opposing to said first substrate;

a wiring provided ~~connected~~ with said second substrate;

a connecting wiring for electrically connecting said wiring of the second substrate to said thin film transistor over said first substrate, wherein said connecting wiring comprises ~~comprising~~: a metallic film over said first substrate~~[[;]]~~ and a transparent conductive film over said metallic film;

~~an anisotropic conductive film for electrically connecting said wiring connected with said second substrate and said connecting wiring; and~~

~~an insulating film being in contact with a side edge of said metallic film,~~

wherein said metallic film has a taper shape,

wherein the wiring of the second substrate is connected to a portion of the connecting wiring, and

wherein both side edges of the portion of the connecting wiring are in contact with the insulating film

~~wherein said thin film transistor comprises a semiconductor film, and~~

~~wherein said metallic film comprises a same material as that of said source wiring.~~

32. (Previously Presented) A semiconductor device according to claim 31 wherein the insulating film comprises a same material as that contained in an insulating film between a gate wiring and a source wiring of the thin film transistor.

33.-34. (Canceled)

35. (Previously Presented) A semiconductor device according to claim 31 wherein a thickness of the metallic film is between 100 nm and 1 μ m.

36. (Previously Presented) A semiconductor device according to claim 31 wherein the metallic film comprises Al.

37. (Previously Presented) A semiconductor device according to claim 31 wherein the metallic film comprises W.

38. (Previously Presented) A semiconductor device according to claim 31 wherein the metallic film is a lamination film comprising a W layer and a layer comprising W and N.

39. (Previously Presented) A semiconductor device according to claim 31 wherein a thickness of the transparent conductive film is between 50 nm and 0.5 μ m.

40. (Previously Presented) A semiconductor device according to claim 31 wherein the transparent conductive film comprises zinc oxide.

41. (Previously Presented) A semiconductor device according to claim 31 wherein the transparent conductive film comprises zinc oxide and indium oxide.

42. (Previously Presented) The semiconductor device according to claim 31 wherein said semiconductor device is one of a liquid crystal display device and EL display device.

43. (Currently Amended) A semiconductor device comprising:
a first substrate;
a thin film transistor over said first substrate;
~~a source region, a drain region and a channel formation region in said thin film transistor;~~
~~a source wiring electrically connected with said source region;~~
a second substrate opposing to said first substrate;
a wiring provided ~~connected~~ with said second substrate;
a connecting wiring for electrically connecting said wiring of the second substrate to said thin film transistor over said first substrate, wherein said connecting wiring comprises ~~comprising~~: a metallic film over said first substrate[;]] and a transparent conductive film over said metallic film;
~~an anisotropic conductive film for electrically connecting said wiring connected with said second substrate and said connecting wiring;~~
a column-shape spacer formed over said thin film transistor for maintaining a space between said first substrate and said second substrate; and
an insulating film ~~being in contact with a side edge of said metallic film comprising a same material as that of the column-shape spacer,~~
wherein said metallic film has a taper shape,
wherein the wiring of the second substrate is connected to a portion of the connecting wiring, and

wherein both side edges of the portion of the connecting wiring are in contact with the insulating film

~~wherein said thin film transistor comprises a semiconductor film, and
wherein said metallic film comprises a same material as that of said source wiring.~~

44.-45. (Canceled)

46. (Previously Presented) A semiconductor device according to claim 43 wherein a thickness of the metallic film is between 100 nm and 1 μ m.

47. (Previously Presented) A semiconductor device according to claim 43 wherein the metallic film comprises Al.

48. (Previously Presented) A semiconductor device according to claim 43 wherein the metallic film comprises W.

49. (Previously Presented) A semiconductor device according to claim 43 wherein the metallic film is a lamination film comprising a W layer and a layer comprising W and N.

50. (Previously Presented) A semiconductor device according to claim 43 wherein a thickness of the transparent conductive film is between 50 nm and 0.5 μ m.

51. (Previously Presented) A semiconductor device according to claim 43 wherein the transparent conductive film comprises zinc oxide.

52. (Previously Presented) A semiconductor device according to claim 43 wherein the transparent conductive film comprises zinc oxide and indium oxide.

53. (Previously Presented) The semiconductor device according to claim 43 wherein said semiconductor device is one of a liquid crystal display device and EL display device.

54. (Canceled)

55. (Previously Presented) A semiconductor device according to claim 31 wherein the connecting wiring is formed of the same materials as those of a source wiring and a drain wiring of the thin film transistor.

56. (Previously Presented) A semiconductor device according to claim 43 wherein the connecting wiring is formed of the same materials as those of a source wiring and a drain wiring of the thin film transistor.

57.-58. (Canceled)